



## ST1802FH

### HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

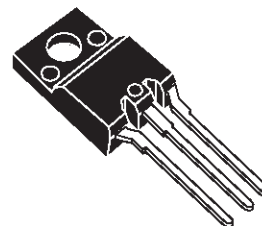
- NEW Fully Plastic TO-220 for HIGH VOLTAGE APPLICATIONS
- NEW SERIES, ENHANCED PERFORMANCE
- EASY MOUNTING
- HIGH VOLTAGE CAPABILITY ( > 1500 V )
- HIGH SWITCHING SPEED
- TIGHTER  $h_{fe}$  CONTROL
- IMPROVED RUGGEDNESS
- FULLY MOLDED ISOLATED PACKAGE 2KV DC ISOLATION (U.L. COMPLIANT)
- CREEPAGE DISTANCE PATH > 4 mm

#### APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOR TV

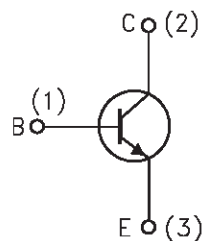
#### DESCRIPTION

The device is manufactured using Diffused Collector Technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.



TO-220FH

#### INTERNAL SCHEMATIC DIAGRAM



SC06960

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	600	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	7	V
$I_C$	Collector Current	10	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	15	A
$I_B$	Base Current	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	40	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

THERMAL DATA

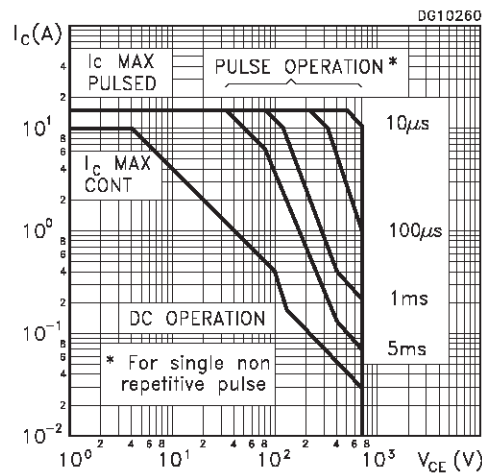
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.125	°C/W
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ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

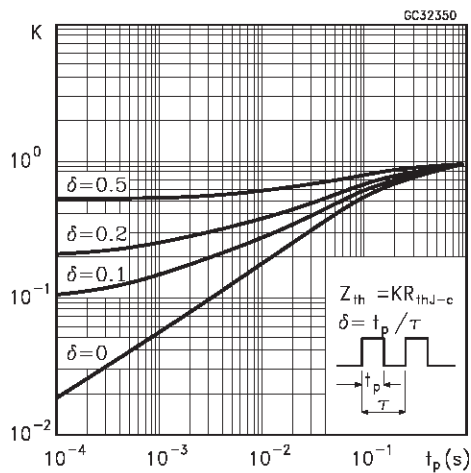
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1500 V V <sub>CE</sub> = 1500 V T <sub>j</sub> = 125 °C			1 2	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 7 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA L = 25 mH	600			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4 A I <sub>B</sub> = 0.8 A I <sub>C</sub> = 4 A I <sub>B</sub> = 1.2 A			5 1.5	V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5 A I <sub>B</sub> = 1 A			1.2	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 1 A V <sub>CE</sub> = 5 V I <sub>C</sub> = 5 A V <sub>CE</sub> = 5 V	4	25	9	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 4 A I <sub>Bon(END)</sub> = 1 A L <sub>B</sub> = 5 µH V <sub>BB</sub> = -2.5 V f = 16 KHz		5 0.3	6 0.5	µs µs

\* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

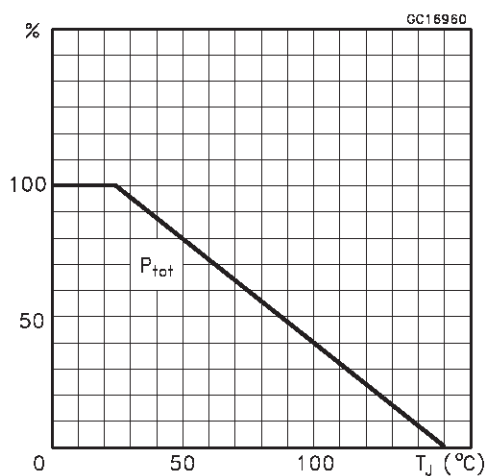
Safe Operating Area



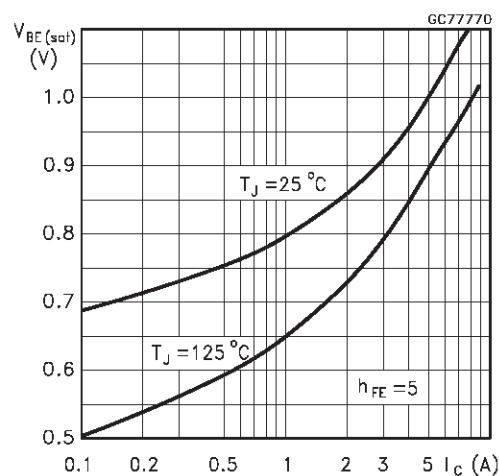
Thermal Impedance



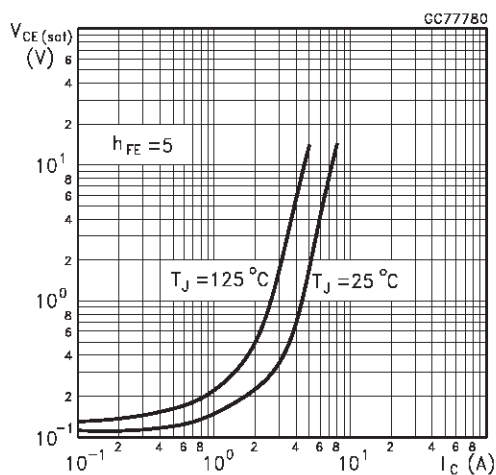
Derating Curve



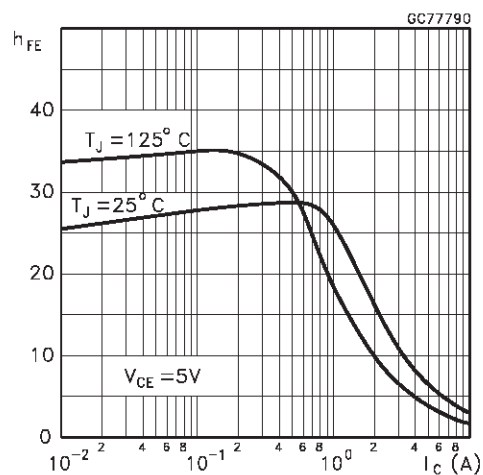
Base Emitter Saturation Voltage



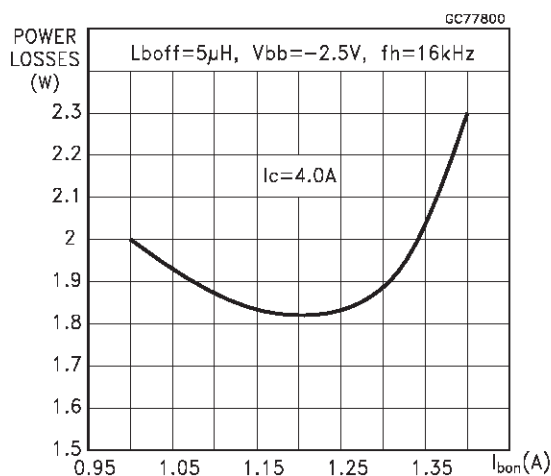
Collector Emitter Saturation Voltage



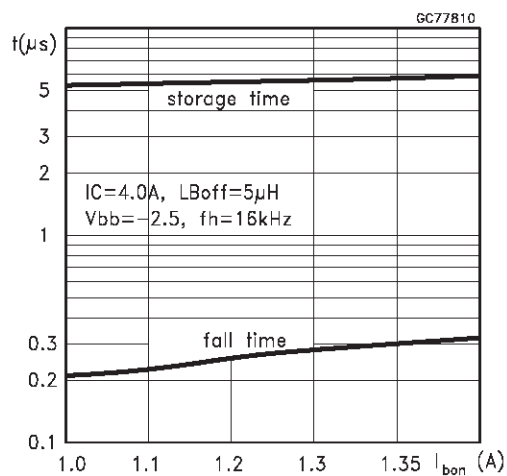
DC Current Gain



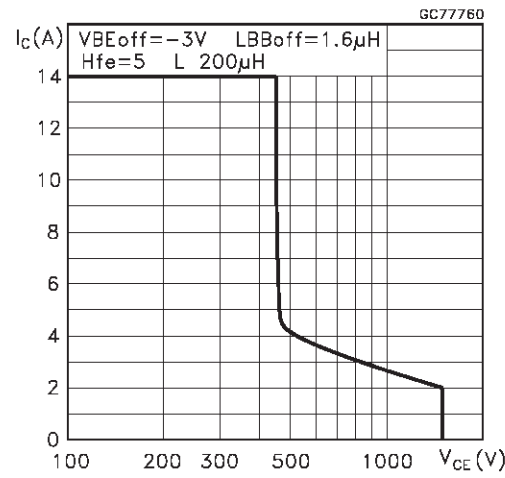
Power Losses At 16 KHz



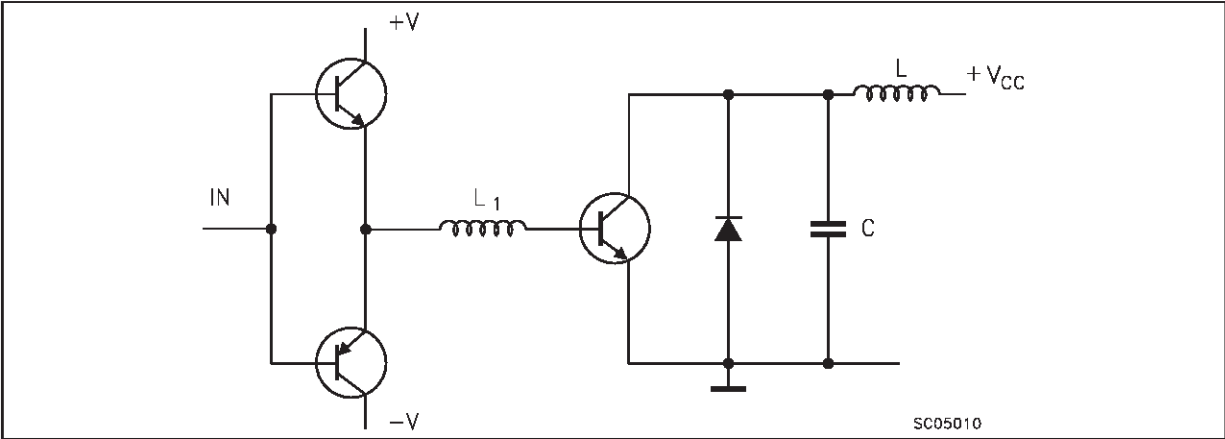
Switching Time Inductive Load



Reverse Biased SOA

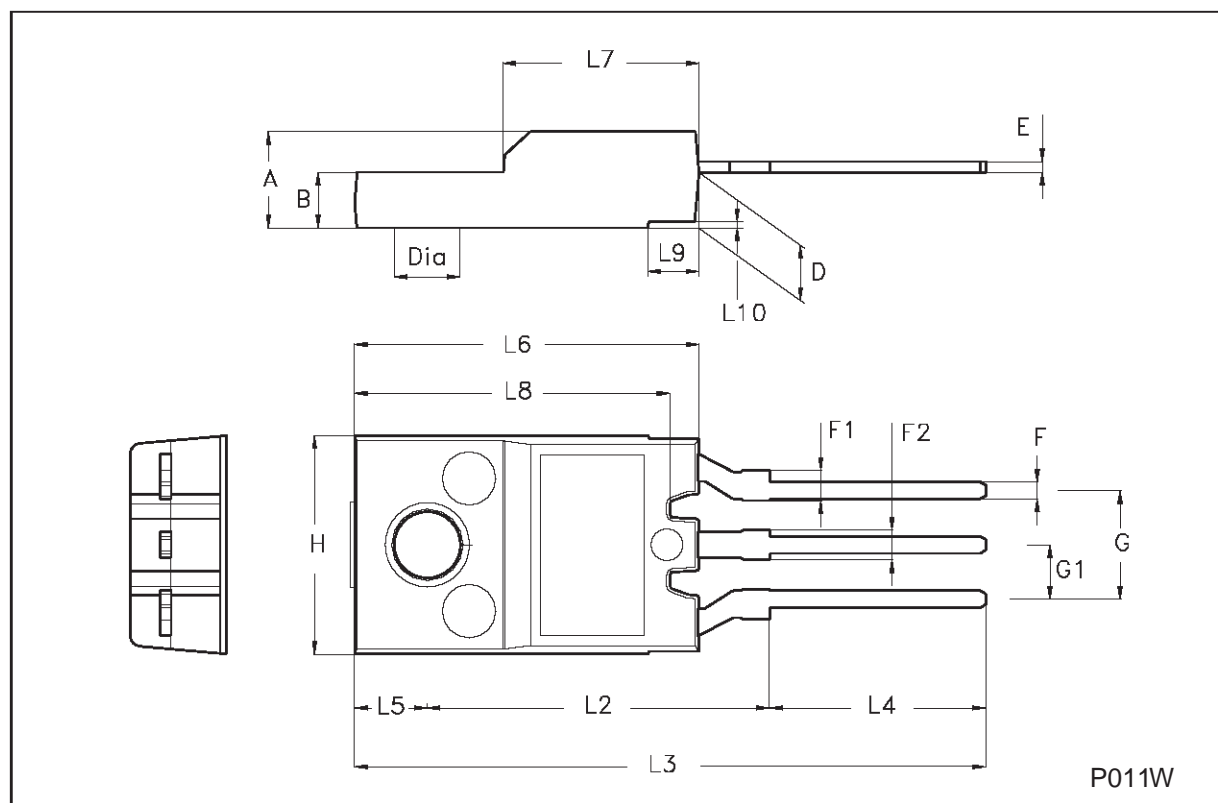


Inductive Load Switching Test Circuits.



**TO-220FH (Fully plastic High voltage) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.3		1.8	0.051		0.070
F2	1.3		1.8	0.051		0.070
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L5		3.4			0.134	
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
L8	14.5		15	0.570		0.590
L9		2.4			0.094	



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